

1. Record Nr.	UNINA9910808289103321
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Titolo	GaN transistors for efficient power conversion // Alex Lidow [and three others]
Pubbl/distr/stampa	Chichester, England : , : Wiley, , 2015 ©2015
ISBN	1-118-84479-3 1-118-84478-5 1-118-84477-7
Edizione	[Second edition.]
Descrizione fisica	1 online resource (269 pages)
Collana	THEi Wiley ebooks.
Disciplina	621.3815/284
Soggetti	Field-effect transistors Gallium nitride
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references at the end of each chapters and index.
Nota di contenuto	GaN Transistors for Efficient Power Conversion; Contents; Foreword; Acknowledgments; 1 GaN Technology Overview; 1.1 Silicon Power MOSFETs 1976-2010; 1.2 The GaN Journey Begins; 1.3 Why Gallium Nitride?; 1.3.1 Band Gap (Eg); 1.3.2 Critical Field (Ecrit); 1.3.3 On-Resistance (RDS(on)); 1.3.4 The Two-Dimensional Electron Gas; 1.4 The Basic GaN Transistor Structure; 1.4.1 Recessed Gate Enhancement-Mode Structure; 1.4.2 Implanted Gate Enhancement-Mode Structure; 1.4.3 pGaN Gate Enhancement-Mode Structure; 1.4.4 Cascode Hybrid Enhancement-Mode Structure; 1.4.5 Reverse Conduction in HEMT Transistors 1.5 Building a GaN Transistor 1.5.1 Substrate Material Selection; 1.5.2 Growing the Heteroepitaxy; 1.5.3 Processing the Wafer; 1.5.4 Making Electrical Connection to the Outside World; 1.6 Summary; References; 2 GaN Transistor Electrical Characteristics; 2.1 Introduction; 2.2 Key Device Parameters; 2.2.1 Breakdown Voltage (BVDSS) and Leakage Current (IDSS); 2.2.2 On-Resistance (RDS(on)); 2.2.3 Threshold Voltage (VGS(th) or Vth); 2.3 Capacitance and Charge; 2.4 Reverse Conduction; 2.5 Thermal Resistance; 2.6 Transient Thermal Impedance; 2.7 Summary; References; 3 Driving GaN Transistors

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Sommario/riassunto

The first edition of GaN Transistors for Efficient Power Conversion was self-published by EPC in 2012, and is currently the only other book to discuss GaN transistor technology and specific applications for the technology. More than 1,200 copies of the first edition have been sold through Amazon or distributed to selected university professors, students and potential customers, and a simplified Chinese translation is also available. The second edition has expanded emphasis on applications for GaN transistors and design considerations. This textbook provides technical and application-
